

ABSTRACT OF THE DISCLOSURE

A semiconductor memory device comprises memory banks each including a memory cell array and a control circuit for the
5 memory cell array and an interface circuit shared by the plural memory banks. The semiconductor memory device is adapted for performing reading of data from the plural memory banks and rewriting of data to the memory banks. In an operation mode for performing the reading, processings A1 to A4 are performed.
10 In an operation mode for performing the rewriting, processings B1 to B3 are performed.